

MMST3906

PNP Plastic-
Encapsulate Transistor

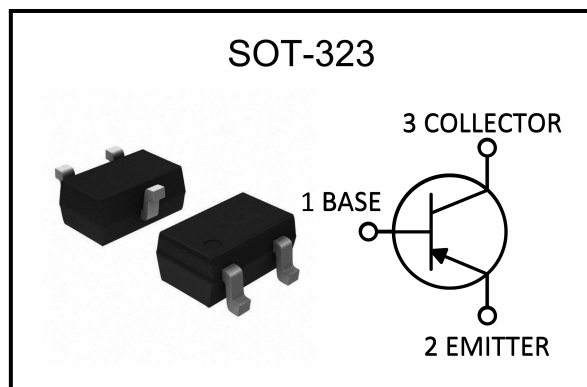
Features

- $V_{CE} = -40V$
- $I_C = -0.2A$
- $f_T = 250MHz$ @ $V_{CE} = -20V$, $I_C = -10mA$, $f = 100MHz$

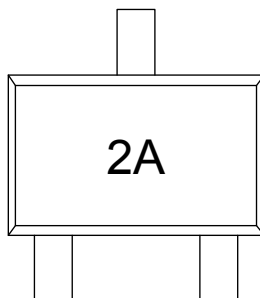
Description

- As complementary type the NPN transistor MMST3904 is recommended
- Epitaxial planar die construction
- SOT-323 Plastic Package.

Package



Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
MMST3906	SOT-323	2A	3K	Tape and reel

Absolute Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_{tot}	Total Device Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	625	$^\circ C/W$
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ C$

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

Revision: 2022-Jan-1-A



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

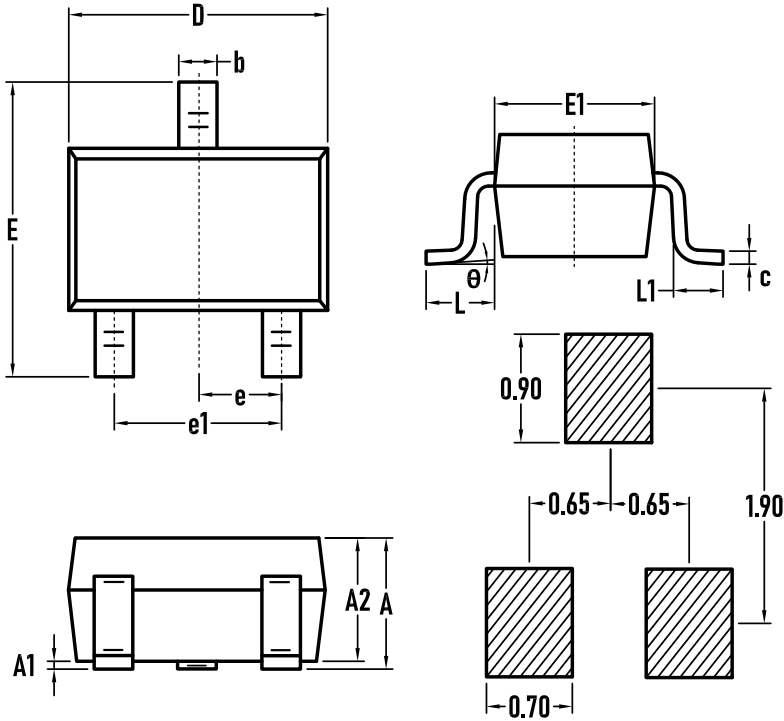
Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V_{CBO}	Collector-base breakdown voltage	$I_C=-10\mu\text{A}, I_E=0$	-50	—	—	V
V_{CEO}	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-40	—	—	
V_{EBO}	Emitter-base breakdown voltage	$I_E=-10\mu\text{A}, I_C=0$	-5	—	—	
I_{CBO}	Collector cut-off current	$V_{CB}=-40\text{V}, I_E=0$	—	—	-0.1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5\text{V}, I_C=0$	—	—	-0.1	
$h_{FE(1)}$	DC current gain	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100	—	300	—
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=-50\text{mA}, I_B=-5\text{mA}$	—	—	-0.3	V
f_T	Transition frequency	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHZ}$	250	—	—	MHZ
t_d	Delay time	$V_{CC}=-3\text{V}, V_{BE}=-0.5\text{V},$ $I_C=-10\text{mA}, I_{B1}=-I_{B2}=-1\text{mA}$	—	—	35	nS
t_r	Rise time		—	—	35	nS
t_f	Fall time	$V_{CC}=-3\text{V}, I_C=-10\text{mA},$ $I_{B1}=-I_{B2}=-1\text{mA}$	—	—	75	nS
t_s	Storage time		—	—	225	nS



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Outline Drawing - SOT-323



SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.90	0.95	1.00
b	0.20	0.30	0.40
c	0.08	0.12	0.15
D	2.00	2.10	2.20
E	2.15	2.30	2.45
E1	1.15	1.25	1.35
e	0.650Typ.		
e1	1.20	1.30	1.40
L1	0.26	0.36	0.46
L	0.525REF		
θ	0°	4°	8°

